

IZO(In_2O_3 -ZnO) Thin Film deposition by continuous Flow Micro Reactor

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In this paper, we have prepared n-type transparent IZO (In_2O_3 -ZnO) thin films through continuous Flow Reactor Process(CFR) which has a control system of flux of precursors and reaction temperatures. In order to apply IZO thin films for the fabrication of Flexible display devices, we have investigated annealing processes including normal air annealing and wet annealing processes under the different conditions. The structural, optical and electrical properties of the obtained IZO thin films have been characterized, respectively. The IZO thin film showed suitable performance for thin film transistor device (TFT).